PATENT ABSTRACTS OF JAPAN

(11)Publication number:

08-171101

(43)Date of publication of application: 02.07.1996

(51)Int.CI.

G02F 1/136 G02F 1/1335

(21)Application number: 06-315061

(71)Applicant: TOSHIBA CORP

(22)Date of filing:

19.12.1994

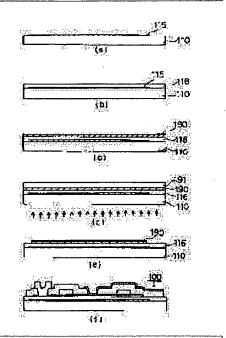
(72)Inventor: KOBAYASHI MICHIYA

(54) PRODUCTION OF LIQUID CRYSTAL DISPLAY DEVICE

(57)Abstract:

PURPOSE: To suppress the generation of the light leakage current of TFT, to surely hold the voltage impressed on liquid crystal when the TFT is off, and to improve the contrast of display images, display performance, etc., by subjecting an active layer to exposing from the rear surface of a substrate with the light shielding film patterns of a lower layer as an exposure mask for photolithography at the time of patterning the active layer.

CONSTITUTION: The light shielding film 115 having a thickness of 300nm and consisting of Cr is formed on a quartz substrate 110. A first interlayer insulating film 116 consisting of SiO2 is formed on this light shielding film 115. First P-Si having the same plane shape as the plane shape of the light shielding film 115 is formed on this interlayer insulating film 116 and is patterned by the rear surface exposure using the light shielding film 115 as the mask to form the active layer. As the result, the plane shape of the active layer of TFT is so formed to nearly the same shape as the rear surface shape of the light shielding film 115 and in such a manner that the mispositioning does not arise. Light is, therefore, reflected right under the TFT and the admission of the light into the TFT is prevented. The light leak current of the TFT is thus suppressed.



LEGAL STATUS

[Date of request for examination]

[Date of sending the examiner's decision of rejection]

[Kind of final disposal of application other than the examiner's decision of rejection or application converted registration]

[Date of final disposal for application]

[Patent number]

[Date of registration]

[Number of appeal against examiner's decision of rejection]

[Date of requesting appeal against examiner's decision of rejection]

[Date of extinction of right]

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